Silicon NPN Power Transistors 2SC2920

DESCRIPTION

·With TO-3 package
·High breakdown voltage
·Fast switching speed.
·Wide area of safe operation

APPLICATIONS

·For switching regulator applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

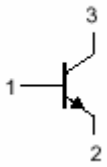

Fig.1 simplified outline (TO-3) and symbol

ABSOLUTE MAXIMUM RATINGS(T_C=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	450	V
V_{CEO}	Collector-emitter voltage	Open base	400	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		15	A
P_C	Collector power dissipation	T_C=25□	150	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=5mA ; R_{BE}=∞	400			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=1mA ; I_E=0	450			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=1mA ; I_C=0	7			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	I_C=10A; I_B=1A			1.0	V
$V_{BE(sat)}$	Base-emitter saturation voltage	I_C=10A; I_B=1A			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=450V ;I_E=0			100	μA
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			100	μA
h_{FE}	DC current gain	I_C=10A ; V_{CE}=2V	10		30	
f_T	Transition frequency	I_C=2A ; V_{CE}=10V		30		MHz
C_{OB}	Collector output capacitance	I_E=0 ; V_{CB}=10V,f=1MHz		240		pF

PACKAGE OUTLINE

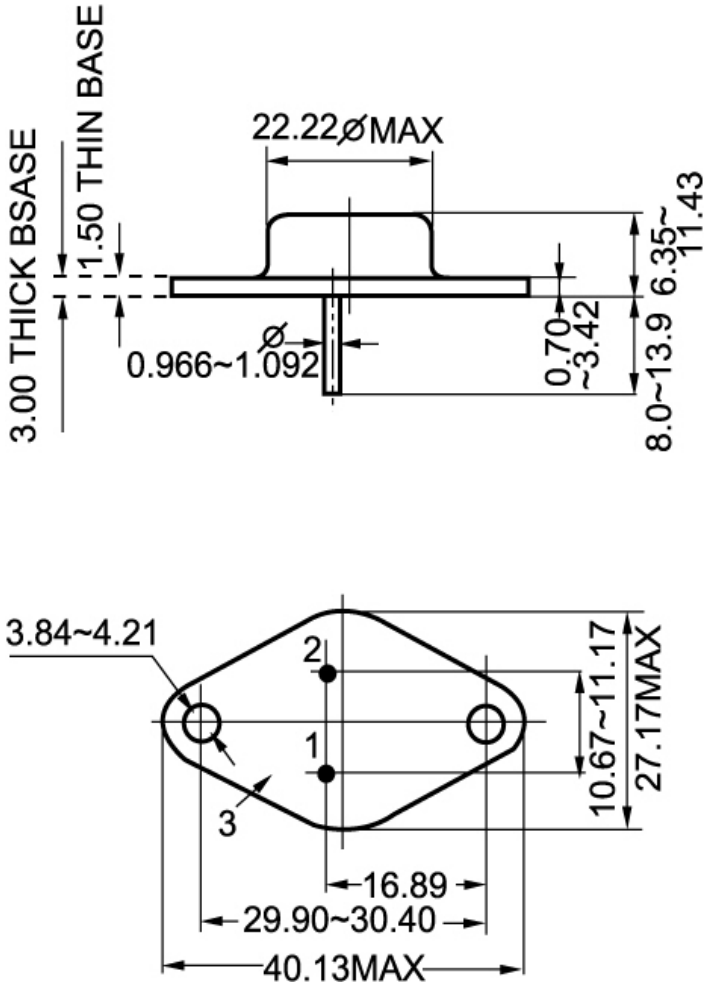

Fig.2 outline dimensions (unindicated tolerance:±0.1mm)